

## 62 mm C-Series module with CoolSiC™ Trench MOSFET

### Features

- Electrical features
  - $V_{DS} = 2000\text{ V}$
  - $I_{DN} = 300\text{ A} / I_{DRM} = 600\text{ A}$
  - Low switching losses
  - High current density
- Mechanical features
  - 4 kV AC 1 min insulation

### Potential applications

- UPS systems
- DC/DC converter
- High-frequency switching application
- Solar applications

### Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

### Description

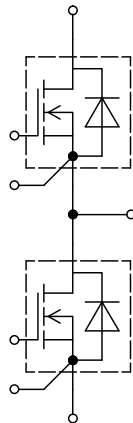


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## 1 Package

**Table 1** Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	$V_{ISOL}$	RMS, $f = 50 \text{ Hz}$ , $t = 1 \text{ min}$	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	$Al_2O_3$	
Creepage distance	$d_{Creep}$	terminal to heatsink	29.0	mm
Creepage distance	$d_{Creep}$	terminal to terminal	23.0	mm
Clearance	$d_{Clear}$	terminal to heatsink	23.0	mm
Clearance	$d_{Clear}$	terminal to terminal	11.0	mm
Comparative tracking index	$CTI$		> 400	
Relative thermal index (electrical)	$RTI$	housing	140	°C

**Table 2** Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	$L_{sCE}$			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$ , per switch		0.475		mΩ
Storage temperature	$T_{stg}$		-40		125	°C
Mounting torque for module mounting	$M$	- Mounting according to valid application note	M6, Screw	3	6	Nm
Terminal connection torque	$M$	- Mounting according to valid application note	M6, Screw	2.5	5	Nm
Weight	$G$			340		g

## 2 MOSFET, T1 / T2

**Table 3** Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage	$V_{DSS}$	$T_{vj} = 25 \text{ °C}$	2000	V
Implemented drain current	$I_{DN}$		300	A
Continuous DC drain current	$I_{DDC}$	$T_{vj} = 175 \text{ °C}$ , $V_{GS} = 18 \text{ V}$ $T_C = 25 \text{ °C}$	280	A
Repetitive peak drain current	$I_{DRM}$	verified by design, $t_p$ limited by $T_{vjmax}$	600	A

(table continues...)

**Table 3 (continued) Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Gate-source voltage, max. transient voltage	$V_{GS}$	$D < 0.01$	-10/23	V
Gate-source voltage, max. static voltage	$V_{GS}$		-7/20	V

**Table 4 Recommended values**

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		18	V
Off-state gate voltage	$V_{GS(off)}$		-3	V

**Table 5 Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	$I_D = 300\text{ A}$	$V_{GS} = 18\text{ V}, T_{vj} = 25\text{ °C}$		3.5	5.3	mΩ
			$V_{GS} = 18\text{ V}, T_{vj} = 125\text{ °C}$		7.3		
			$V_{GS} = 18\text{ V}, T_{vj} = 175\text{ °C}$		10.4		
Gate threshold voltage	$V_{GS(th)}$	$I_D = 168\text{ mA}, V_{DS} = V_{GS}, T_{vj} = 25\text{ °C},$ (tested after 1ms pulse at $V_{GS} = +20\text{ V}$ )		3.45	4.3	5.15	V
Total gate charge	$Q_G$	$V_{DD} = 1200\text{ V}, V_{GS} = -3/18\text{ V}$			1.17		μC
Internal gate resistor	$R_{Gint}$	$T_{vj} = 25\text{ °C}$			1.2		Ω
Input capacitance	$C_{ISS}$	$f = 100\text{ kHz}, V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		36.1		nF
Output capacitance	$C_{OSS}$	$f = 100\text{ kHz}, V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.845		nF
Reverse transfer capacitance	$C_{rss}$	$f = 100\text{ kHz}, V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		0.061		nF
$C_{OSS}$ stored energy	$E_{OSS}$	$V_{DS} = 1200\text{ V}, V_{GS} = -3/18\text{ V}, T_{vj} = 25\text{ °C}$			1520		μJ
Drain-source leakage current	$I_{DSS}$	$V_{DS} = 2000\text{ V}, V_{GS} = -3\text{ V}$	$T_{vj} = 25\text{ °C}$		0.06	527	μA
Gate-source leakage current	$I_{GSS}$	$V_{DS} = 0\text{ V}, T_{vj} = 25\text{ °C}$	$V_{GS} = 20\text{ V}$			400	nA
Turn-on delay time (inductive load)	$t_{d on}$	$I_D = 300\text{ A}, R_{Gon} = 7.1\text{ Ω}, V_{DD} = 1200\text{ V}, V_{GS} = -3/18\text{ V}$	$T_{vj} = 25\text{ °C}$		204		ns
			$T_{vj} = 125\text{ °C}$		187		
			$T_{vj} = 175\text{ °C}$		181		

(table continues...)

**Table 5** (continued) **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time (inductive load)	$t_r$	$I_D = 300\text{ A}$ , $R_{Gon} = 7.1\ \Omega$ , $V_{DD} = 1200\text{ V}$ , $V_{GS} = -3/18\text{ V}$	$T_{vj} = 25\text{ °C}$	219		ns
			$T_{vj} = 125\text{ °C}$	195		
			$T_{vj} = 175\text{ °C}$	194		
Turn-off delay time (inductive load)	$t_{d\ off}$	$I_D = 300\text{ A}$ , $R_{Goff} = 4.3\ \Omega$ , $V_{DD} = 1200\text{ V}$ , $V_{GS} = -3/18\text{ V}$	$T_{vj} = 25\text{ °C}$	256		ns
			$T_{vj} = 125\text{ °C}$	282		
			$T_{vj} = 175\text{ °C}$	296		
Fall time (inductive load)	$t_f$	$I_D = 300\text{ A}$ , $R_{Goff} = 4.3\ \Omega$ , $V_{DD} = 1200\text{ V}$ , $V_{GS} = -3/18\text{ V}$	$T_{vj} = 25\text{ °C}$	80.3		ns
			$T_{vj} = 125\text{ °C}$	82.1		
			$T_{vj} = 175\text{ °C}$	84.2		
Turn-on energy loss per pulse	$E_{on}$	$I_D = 300\text{ A}$ , $V_{DD} = 1200\text{ V}$ , $L_\sigma = 25\text{ nH}$ , $V_{GS} = -3/18\text{ V}$ , $R_{Gon} = 7.1\ \Omega$ , $di/dt = 3.4\text{ kA}/\mu\text{s}$ ( $T_{vj} = 175\text{ °C}$ )	$T_{vj} = 25\text{ °C}$	45.5		mJ
			$T_{vj} = 125\text{ °C}$	46.5		
			$T_{vj} = 175\text{ °C}$	50.5		
Turn-off energy loss per pulse	$E_{off}$	$I_D = 300\text{ A}$ , $V_{DD} = 1200\text{ V}$ , $L_\sigma = 25\text{ nH}$ , $V_{GS} = -3/18\text{ V}$ , $R_{Goff} = 4.3\ \Omega$ , $dv/dt = 11.4\text{ kV}/\mu\text{s}$ ( $T_{vj} = 175\text{ °C}$ )	$T_{vj} = 25\text{ °C}$	23.7		mJ
			$T_{vj} = 125\text{ °C}$	24.5		
			$T_{vj} = 175\text{ °C}$	25.2		
Thermal resistance, junction to case	$R_{thJC}$	per MOSFET			0.119	K/W
Thermal resistance, case to heat sink	$R_{thCH}$	per MOSFET, $\lambda_{grease} = 1\text{ W}/(\text{m}^2\text{K})$ , $\lambda_{grease} = 1\text{ W}/(\text{m}^2\text{K})$		0.0380		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		175	°C

**Note:** The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2021-13 must be considered to ensure sound operation of the device over the planned lifetime.

$T_{vj,op} > 150\text{ °C}$  is allowed for operation at overload conditions for MOSFET and body diode. For detailed specifications, please refer to AN 2021-13.

### 3 Body diode (MOSFET, T1 / T2)

**Table 6** **Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
DC body diode forward current	$I_{SD}$	$T_{vj} = 175\text{ °C}$ , $V_{GS} = -3\text{ V}$ $T_C = 25\text{ °C}$	235	A

**Table 7**                      **Characteristic values**

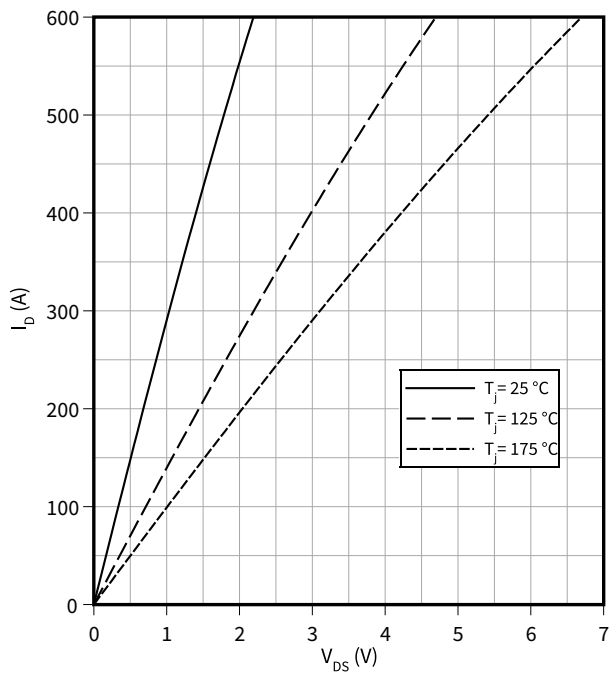
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	$V_{SD}$	$I_{SD} = 300 \text{ A}$ , $V_{GS} = -3 \text{ V}$	$T_{vj} = 25 \text{ °C}$		4.6	6.15	V
			$T_{vj} = 125 \text{ °C}$		4.15		
			$T_{vj} = 175 \text{ °C}$		4		

4 Characteristics diagrams

Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

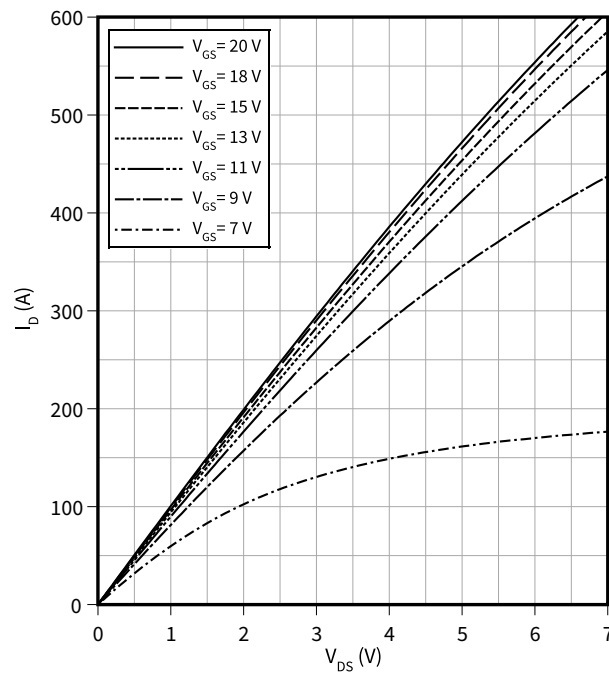
$V_{GS} = 18\text{ V}$



Output characteristic field (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

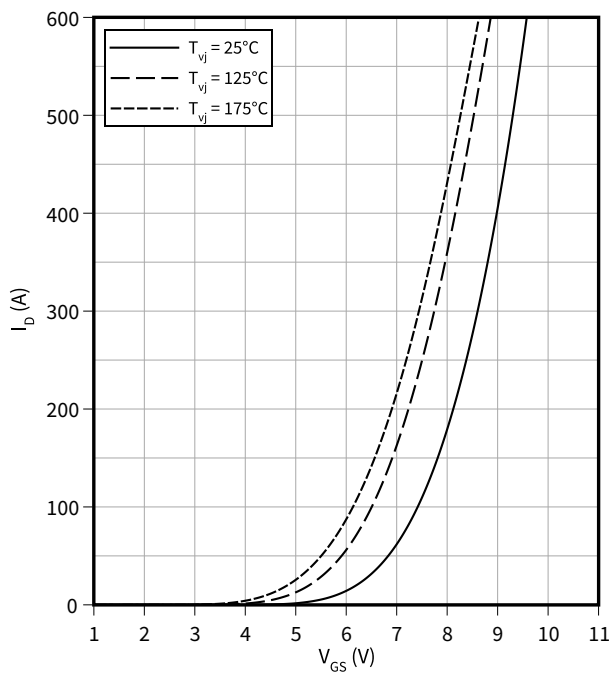
$T_{vj} = 175^\circ\text{C}$



Transfer characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{GS})$

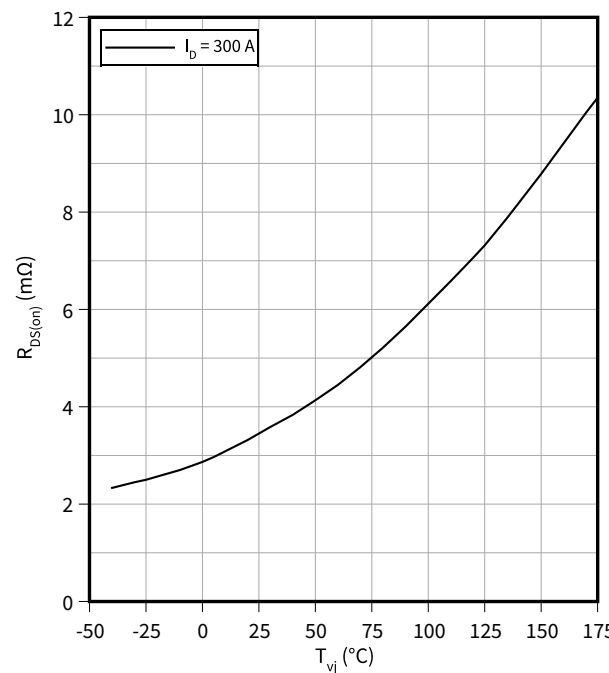
$V_{DS} = 20\text{ V}$



Drain source on-resistance (typical), MOSFET, T1 / T2

$R_{DS(on)} = f(T_{vj})$

$V_{GS} = 18\text{ V}$

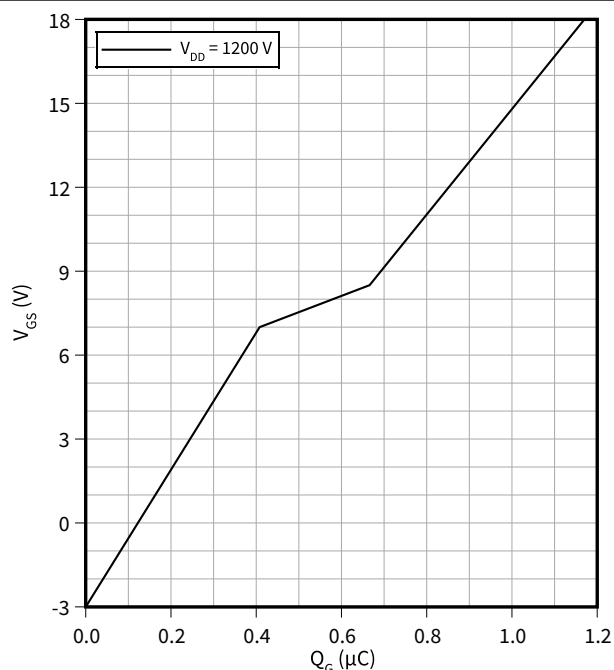


4 Characteristics diagrams

**Gate charge characteristic (typical), MOSFET, T1 / T2**

$$V_{GS} = f(Q_G)$$

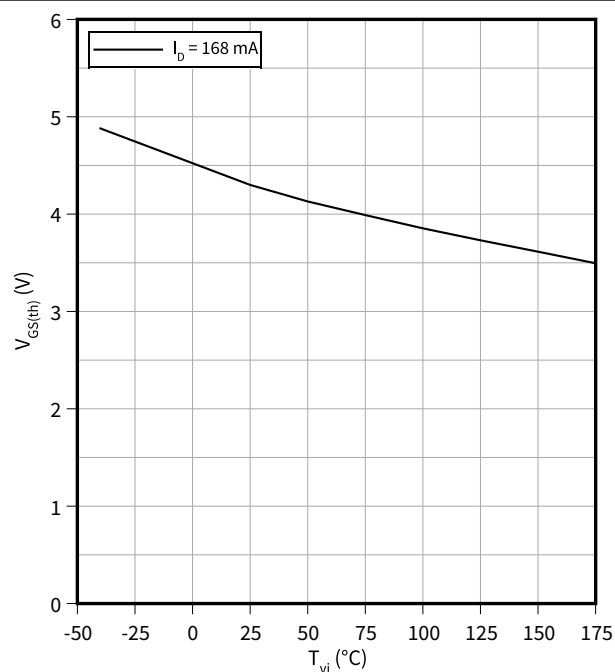
$$I_D = 300 \text{ A}, T_{vj} = 25 \text{ }^{\circ}\text{C}$$



**Gate-source threshold voltage (typical), MOSFET, T1 / T2**

$$V_{GS(th)} = f(T_{vj})$$

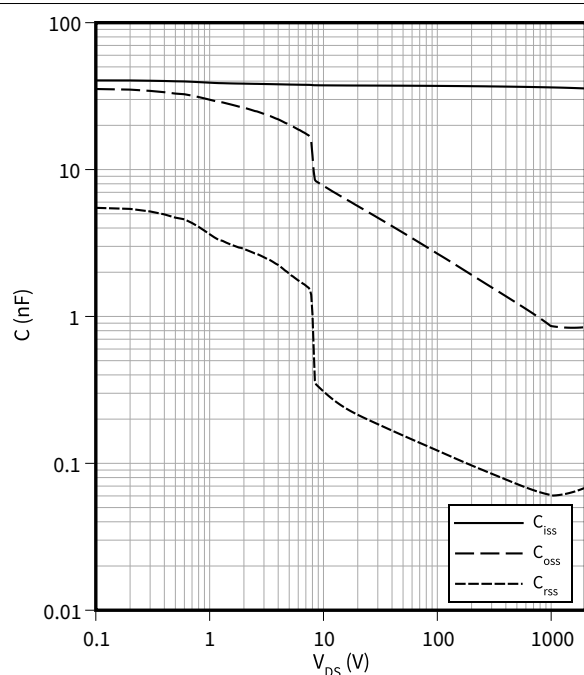
$$V_{GS} = V_{DS}$$



**Capacity characteristic (typical), MOSFET, T1 / T2**

$$C = f(V_{DS})$$

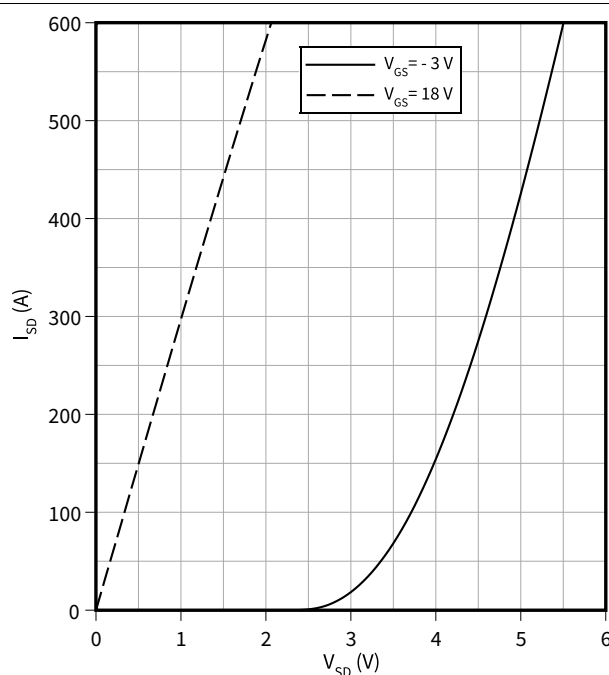
$$f = 100 \text{ kHz}, T_{vj} = 25 \text{ }^{\circ}\text{C}, V_{GS} = 0 \text{ V}$$



**Forward characteristic body diode (typical), MOSFET, T1 / T2**

$$I_{SD} = f(V_{SD})$$

$$T_{vj} = 25 \text{ }^{\circ}\text{C}$$



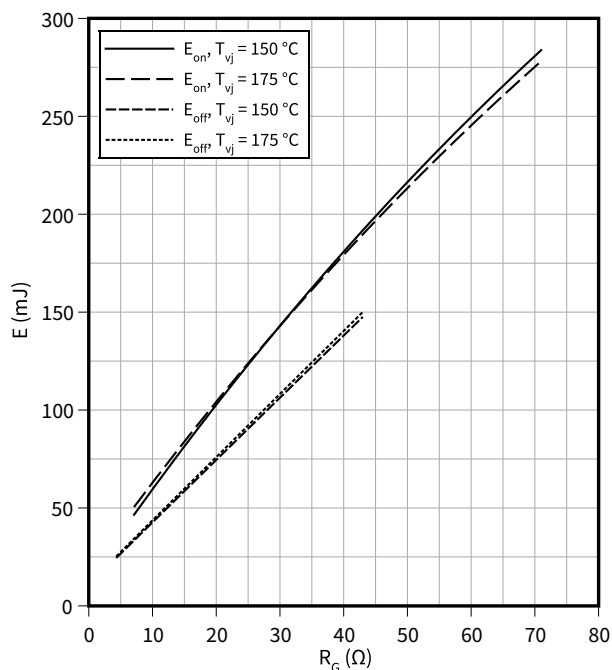


4 Characteristics diagrams

**Switching losses (typical), MOSFET, T1 / T2**

$$E = f(R_G)$$

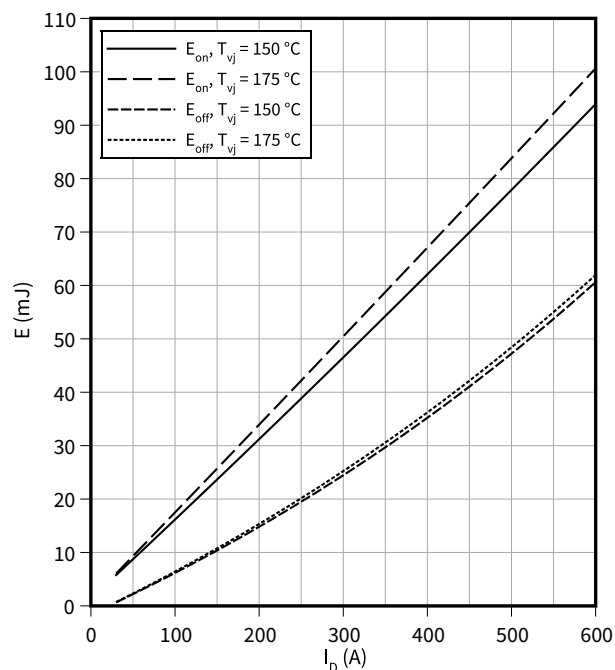
$V_{DD} = 1200 \text{ V}$ ,  $I_D = 300 \text{ A}$ ,  $V_{GS} = -3/18 \text{ V}$



**Switching losses (typical), MOSFET, T1 / T2**

$$E = f(I_D)$$

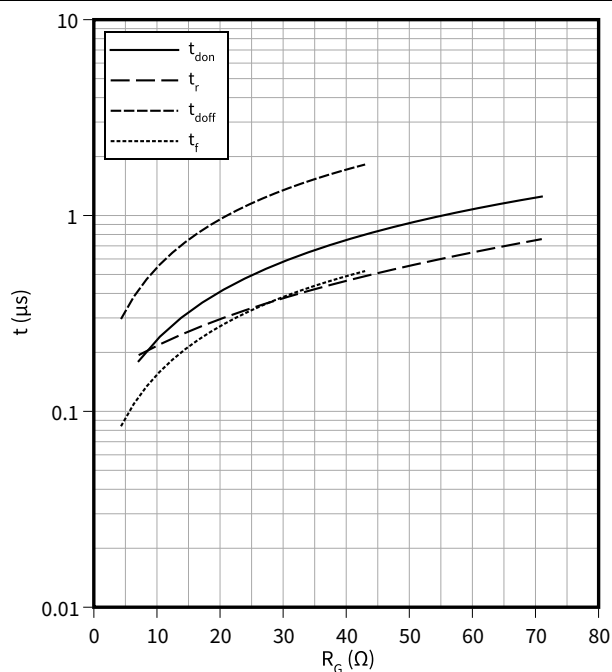
$R_{Goff} = 4.3 \text{ } \Omega$ ,  $R_{Gon} = 7.1 \text{ } \Omega$ ,  $V_{DD} = 1200 \text{ V}$ ,  $V_{GS} = -3/18 \text{ V}$



**Switching times (typical), MOSFET, T1 / T2**

$$t = f(R_G)$$

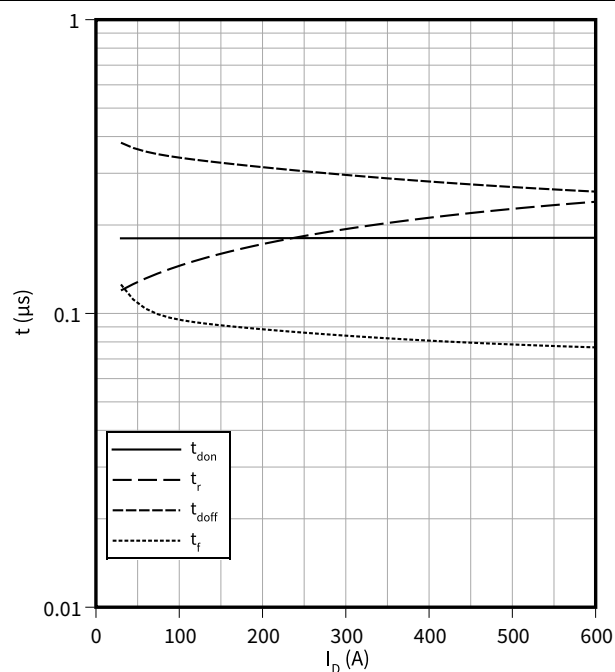
$V_{DD} = 1200 \text{ V}$ ,  $I_D = 300 \text{ A}$ ,  $T_{vj} = 175 \text{ } ^\circ\text{C}$ ,  $V_{GS} = -3/18 \text{ V}$



**Switching times (typical), MOSFET, T1 / T2**

$$t = f(I_D)$$

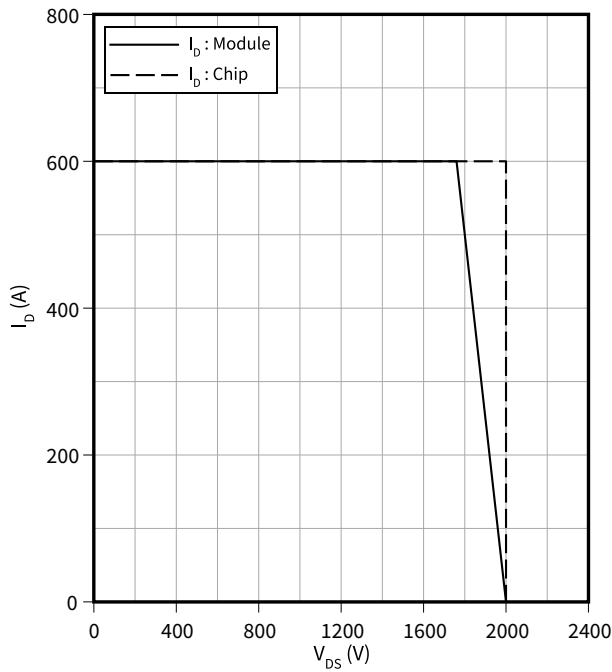
$R_{Goff} = 4.3 \text{ } \Omega$ ,  $R_{Gon} = 7.1 \text{ } \Omega$ ,  $V_{DD} = 1200 \text{ V}$ ,  $T_{vj} = 175 \text{ } ^\circ\text{C}$ ,  $V_{GS} = -3/18 \text{ V}$



4 Characteristics diagrams

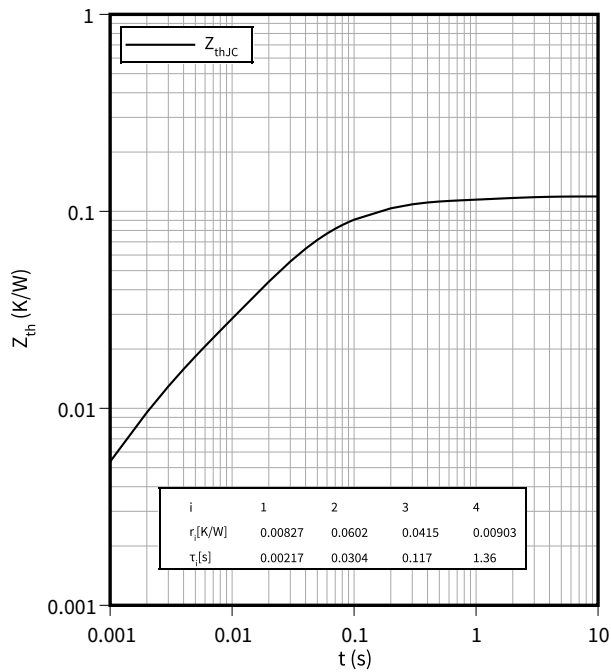
Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

$I_D = f(V_{DS})$   
 $R_{Goff} = 4.3 \, \Omega$ ,  $T_{vj} = 175 \, ^\circ\text{C}$ ,  $V_{GS} = -3/18 \, \text{V}$

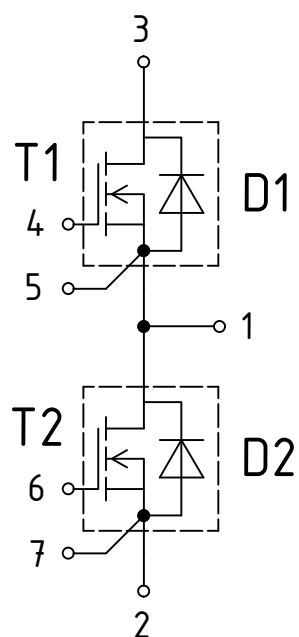


Transient thermal impedance , MOSFET, T1 / T2

$Z_{th} = f(t)$



## 5 Circuit diagram



**Figure 1**



7 Module label code



Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	Content	Digit	Example
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example	<div><div>7154914284655054991153071549142846550549911530</div></div>		

Figure 3

## Revision history

Document revision	Date of release	Description of changes
0.10	2021-06-28	Initial version
0.20	2022-11-09	Target datasheet
1.00	2022-12-22	Final datasheet

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